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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Sunkara et al. )  
)  
Filed: November 10, 2003 ) Examiner:  
) Group Art Unit:  
Serial No: 10/705,687 )  
)  
For: BULK SYNTHESIS OF METAL AND METAL, )  
BASED DIELECTRIC NANOWIRES )  
)  
Atty. Docket No.: AD138/2001 )

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Cynthia Standiford  
(Typed or Printed Name)  
Cynthia Standiford  
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INFORMATION DISCLOSURE DOCUMENT

Enclosed is a list and copies of references considered by Applicant to be pertinent in the  
examination of the above-identified patent application.

Applicant submits this Information Disclosure Statement in accordance with the duty of  
disclosure under 37CFR §1.56 and 1.97-1.98. This Statement is filed in accordance with 37 CFR  
§1.97(b)(3), prior to issuance of a First Office.

Applicants(s) submitted herewith patents, publications or other information of which they  
are aware, which they believe may be material to the examination of this application and in respect

of which there may be a duty to disclose in accordance with 37 CFR 1.56. While this Information Disclosure Statement may be "material" pursuant to 37 CFR 1.56 it is not intended to constitute an admission that any patent, publication or other information referred to therein is "Prior art" for this invention unless specifically designated as such. In accordance with 37 CFR 1.97(b) the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56 (a) exists.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "David W. Carrithers", with a stylized flourish at the end.

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**OTHER PRIOR ART (Including Author, Title, Date Pertinent Pages, ETC.)**

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Examiner Signature		Date Considered	
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